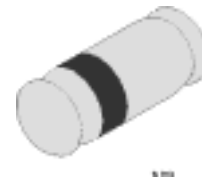




# Switching Diode (FHLL4448)

## Description

- The **FHLL4448** is designed for high-speed switching application in hybrid thick-and-thin-film circuits.
- Small surface mouting type.( **LL-34** )



## ABSOLUTE MAXIMUM RATINGS 最大额定值( $T_A=25$ )

| RATING  | Symbol    | Value       | Unit |
|---|-----------|-------------|------|
| Reverse Voltage 反向电压                                  | $V_R$     | 75          | V    |
| Repetitive peak reverse voltage 反向峰值电压                | $V_{RM}$  | 100         | V    |
| Peak forward surge current 正向浪涌电流 (At $t_p=1 \mu s$ ) | $I_{FSM}$ | 2           | A    |
| Repetitive peak forward current 正向峰值电流                | $I_{FRM}$ | 500         | mA   |
| Forward current 正向电流                                  | $I_F$     | 300         | mA   |
| Average forward current 平均正向电流 (At $V_R=0$ )          | $I_{FAV}$ | 150         | mA   |
| Power Dissipation 耗散功率 at $T_A=25$                    | $P_{TOT}$ | 500         | mW   |
| Junction Temperature 结温                               | $T_J$     | 175         |      |
| Storage Temperature Range 存储温度                        | $T_S$     | -65 to +175 |      |

## ELECTRICAL CHARACTERISTICS 电特性( $T_A=25$ )

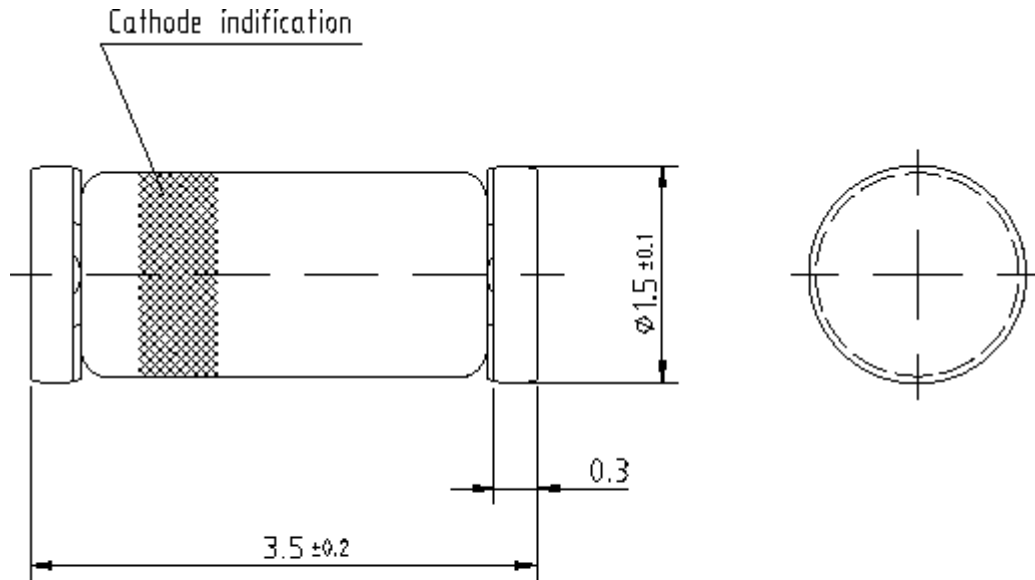
| Characteristic 特性                                  | Symbol      | Min  | Typ  | Max  | Unit    |
|--|-------------|------|------|------|---------|
| Forward Voltage 正向电压                               | $V_F$       | 0.62 | -    | 0.72 | V       |
| At $I_F=5mA$                                       |             | -    | 0.93 | 1.0  |         |
| Leakage current 漏电流                                | $I_R$       | -    | -    | 25   | nA      |
| At $V_R=20v$                                       |             | -    | -    | 5    | $\mu A$ |
| At $V_R=75v$                                       |             | -    | -    | 50   | $\mu A$ |
| At $V_R=20v, T_J=150$                              | $I_R$       | -    | -    | 50   | $\mu A$ |
| Reverse Breakage Voltage 反向击穿电压                    | $V_{(BR)R}$ | 100  | -    | -    | V       |
| $I_R=100 \mu A, t_p/T=0.01, t_p=0.3ms$             |             |      |      |      |         |
| Capacitance 电容                                     | $C_{tot}$   |      |      | 4    | pF      |
| At $V_R=0, f=1.0MHz, V_{HF}=50mV$                  |             |      |      |      |         |
| Reverse Recovery Time 反向回复时间                       | $T_{rr}$    |      |      | 8    | ns      |
| At $I_F=IR=10mA, i_R=1mA$                          |             |      |      | 4    | ns      |
| At $I_F=10mA, V_R=6V, i_R=0.1 \times I_R, R_L=100$ |             |      |      |      |         |
| Junction tambient 热阻                               | $R_{thJA}$  |      |      | 500  | K/W     |
| on PC board 50mmx50mmx1.6mm                        |             |      |      |      |         |
| Rectification Efficiency 整流功率                      | $\eta_r$    | 0.45 |      |      |         |
| at $f=100MHz, V_{HF}=2V,$                          |             |      |      |      |         |

**Notes:** (1)Valid provided that electrodes are kept at ambient temperature.



## Dimensions 封装外形尺寸

Dimensions in mm



Glass case  
Mini MELF / 50D 80  
JEDEC DO 213 AA

961 2070

  
technical drawings  
according to DIN  
specifications